

6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http://www.microsemi.com

### NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/727

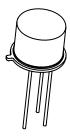
DEVICES			Ī	LEVELS
2N5010	2N5013	2N5010S	2N5013S	JAN
2N5011	2N5014	2N5011S	2N5014S	<b>JANTX</b>
2N5012	2N5015	2N5012S	2N5015S	JANTXV

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = +25^{\circ}C$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit	
Collector-Emitter Voltage 2N5010			500	Vdc
	2N5011		600	Vdc
	2N5012	$V_{CER}$	700	Vdc
	2N5013	V CER	800	Vdc
	2N5014		900	Vdc
	2N5015		1000	Vdc
Collector-Base Voltage	2N5010		500	Vdc
	2N5011		600	Vdc
	2N5012	V	700	Vdc
	2N5013	$V_{CBO}$	800	Vdc
	2N5014		900	Vdc
	2N5015		1000	Vdc
Emitter-Base Voltage		$V_{\mathrm{EBO}}$	5	Vdc
Collector Current		$I_{C}$	200	mAdc
Base Current		$I_{B}$	20	mAdc
Total Power Dissipation	@ $T_A = +25^{\circ}C$ @ $T_C = +25^{\circ}C$	P <sub>t</sub>	1.0 7.0	W
Thermal Resistance, Junction to	Case 1/	$R_{ heta JC}$	20	°C/W
Operating & Storage Junction T	Cemperature Range	$T_j, T_{stg}$	-65 to +200	°C



TO-5 2N5010 thru 2N5015



TO-39 2N5010S thru 2N5015S

#### Note

1/ See 19500/727 for Thermal Derating Curves.



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### ELECTRICAL CHARACTERISTICS ( $T_A = +25$ °C, unless otherwise noted)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current					
$V_{CB} = 400V$	2N5010			10	nAdc
$V_{CB} = 500V$	2N5011			10	nAdc
$V_{CB} = 580V$	2N5012	$I_{CBO1}$		10	nAdc
$V_{CB} = 650V$	2N5013	1CBO1		10	nAdc
$V_{CB} = 700V$	2N5014			10	nAdc
$V_{CB} = 760V$	2N5015			10	nAdc
	@ $T_A = +150^{\circ}C$				
$V_{CB} = 400V$	2N5010			10	uAdc
$V_{CB} = 500V$	2N5011			10	uAdc
$V_{CB} = 588V$	2N5012	$I_{CBO2}$		10	uAdc
$V_{CB} = 650V$	2N5013	0202		10	uAdc
$V_{CB} = 700V$	2N5014			10	uAdc
$V_{CB} = 760V$	2N5015			10	uAdc
Emitter to Base Cutoff Current					
$V_{EB} = 4V$		$I_{EBO}$		20	uAdc
Collector to Base Breakdown Voltage					
$I_C = 0.1 \text{mAdc}$	2N5010		500		Vdc
$I_C = 0.1 \text{mAdc}$	2N5011		600		Vdc
$I_C = 0.1 \text{mAdc}$	2N5012	V <sub>(BR)CBO</sub>	700		Vdc
$I_C = 0.2 \text{mAdc}$	2N5013	V (BR)CBO	800		Vdc
$I_C = 0.2 \text{mAdc}$	2N5014		900		Vdc
$I_C = 0.2 \text{mAdc}$	2N5015		1000		Vdc
Emitter to Base Breakdown Voltage					
$I_C = 0$ mA		$V_{(BR)EBO}$	5		Vdc
$I_E = 0.05 \text{mA}$		(BR)EB0			
Collector to Emitter Breakdown Voltage					
$R_{BE} = 1K\Omega$	2N5010		500		Vdc
$I_C = 0.2 \text{mA}$ , Pulsed	2N5011		600		Vdc
	2N5012	V <sub>(BR)CER</sub>	700		Vdc
	2N5013		800		Vdc
	2N5014		900		Vdc
	2N5015		1000		Vdc
Forward-Current Transfer Ratio					
$I_C = 25 \text{mA}$	2N5010, 2N5011, 2N5012	$h_{\mathrm{FE}1}$	30	180	
$I_C = 20mA$	2N5013, 2N5014, 2N5015	**FEI	30	180	
$V_{CE} = 10V$					
$V_{CE} = 10V$		h-	10		
$I_C = 5mA$		$h_{FE2}$	10		
$V_{CE} = 10V$	@ T = 55°C	h	10		
$I_C = 20 \text{mA}$	@ $T_A = -55^{\circ}C$	$h_{FE3}$	10		



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### ELECTRICAL CHARACTERISTICS ( $T_A = +25^{\circ}C$ , unless otherwise noted) (Cont.)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
$\begin{aligned} & \text{Base-Emitter Saturation Voltage} \\ & I_C = 25\text{mA} \\ & I_C = 20\text{mA} \\ & I_B = 5\text{mA}, \text{Pulsed} \end{aligned}$	2N5010, 2N5011, 2N5012 2N5013, 2N5014, 2N5015	V <sub>BE(SAT)</sub>		1.0 1.0	Vdc Vdc
$\begin{split} & \text{Collector-Emitter Saturation Voltage} \\ & I_C = 25\text{mA} \\ & I_C = 25\text{mA} \\ & I_C = 25\text{mA} \\ & I_C = 20\text{mA} \\ & I_C = 20\text{mA} \\ & I_C = 20\text{mA} \\ & I_B = 5\text{mA}, \text{Pulsed} \end{split}$	2N5010 2N5011 2N5012 2N5013 2N5014 2N5015	$V_{\text{CE(SAT)}}$		1.4 1.5 1.6 1.6 1.6 1.8	Vdc Vdc Vdc Vdc Vdc Vdc

#### DYNAMIC CHARACTERISTICS

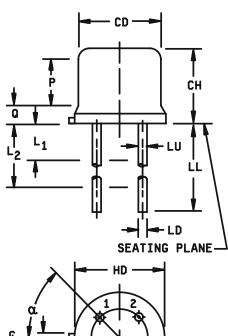
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
$\begin{aligned} &\text{Magnitude of small signal short-circuit forward current transfer ratio} \\ &V_{\text{CE}} = 10 \text{Vdc}, \ I_{\text{C}} = 25 \text{mA}, \ f = 10 \text{MHz} \\ &V_{\text{CE}} = 10 \text{Vdc}, \ I_{\text{C}} = 20 \text{mA}, \ f = 10 \text{MHz} \end{aligned} \qquad \begin{aligned} &2 \text{N} 5010, \ 2 \text{N} 5011, \ 2 \text{N} 5012 \\ &2 \text{N} 5013, \ 2 \text{N} 5014, \ 2 \text{N} 5015 \end{aligned}$	$ \mathrm{h_{fe}} $	1.0 1.0		
Open circuit output capacitance $V_{CB}=10V,I_{E}=0,f=2MHz$	$C_{ m obo}$		30	pF

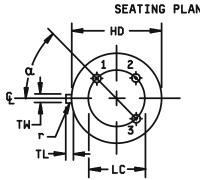


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#### PACKAGE DIMENSIONS





Symbol	Inc	Inches Millimeters		Millimeters	
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	6
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200	) TP	5.08	3 TP	7
LD	.016	.019	0.41	0.48	8,9
LL	See note 14				
LU	.016	.019	0.41	0.48	8,9
L <sub>1</sub>		.050		1.27	8,9
L <sub>2</sub>	.250		6.35		8,9
P	.100		2.54		7
Q		.030		0.76	5
TL	.029	.045	0.74	1.14	3,4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45°	TP	45° TP		7

#### NOTE:

- Dimensions are in inches.
- Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- Dimension LU applies between L<sub>1</sub> and L<sub>2</sub>. Dimension LD applies between L<sub>2</sub> and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- All three leads.
- 10. The collector shall be internally connected to the case.
- 11. Dimension r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- 14. For non-S-suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For Ssuffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

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